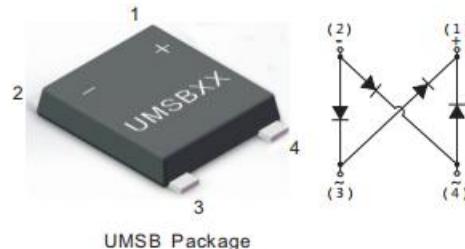


Bridge Rectifier Diode 整流桥**■Features 特点**

Glass passivated chip junction 玻璃钝化结
 High surge current capability 高浪涌电流能力
 Peak Soak Temperature 260°C 峰值浸润温度 260 度
 Package 封装: UMSB

**■Maximum Rating 最大额定值**

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	MSB40B	MSB40D	MSB40G	MSB40J	MSB40K	MSB40M	Unit 单位
Peak Reverse Voltage 反向峰值电压	V _{RRM}	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	V _{R(DC)}	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	V _{R(RMS)}	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I _F	4						A
Peak Surge Current 峰值浪涌电流	I _{FSM}	95						A
Thermal Resistance J-A 结到环境热阻	R _{θJA}	60						°C/W
Junction and Storage Temperature 结温和储藏温度	T _J , T _{stg}	150°C,-55to+150°C						

■Electrical Characteristics 电特性

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压	V _F		1.1		V	I _F =3A
Reverse Current (TA=25°C) 反向电流(TA=125°C)	I _R			5 100	uA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _D		50		pF	V _R =4V,f=1MHz

■Typical Characteristic Curve 典型特性曲线

Fig.1 Average Rectified Output Current Derating Curve

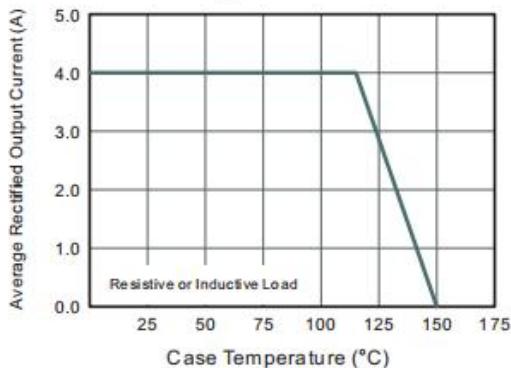


Fig.2 Typical Reverse Characteristics

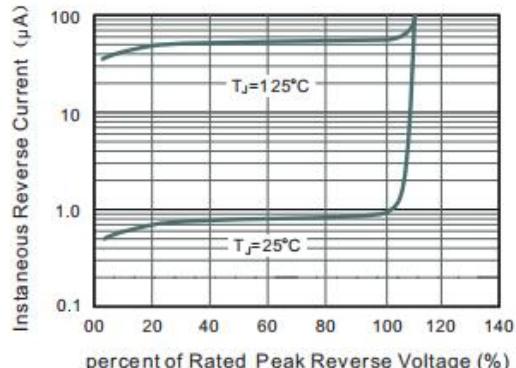


Fig.3 Typical Instantaneous Forward Characteristics

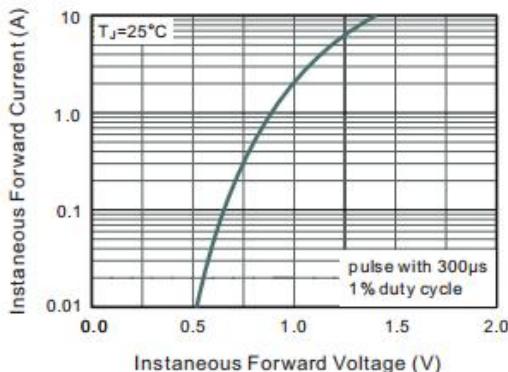


Fig.4 Typical Junction Capacitance

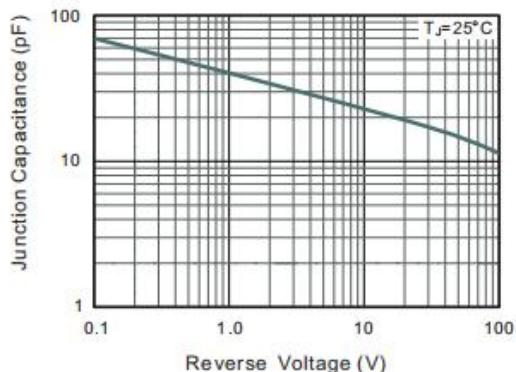


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

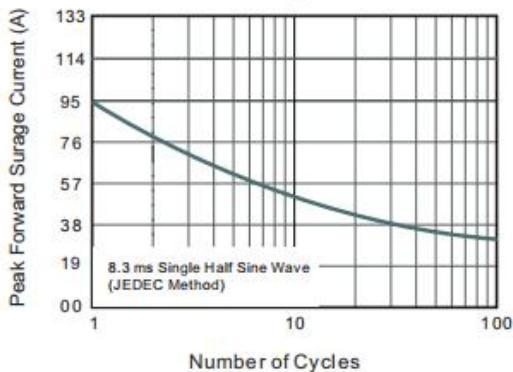
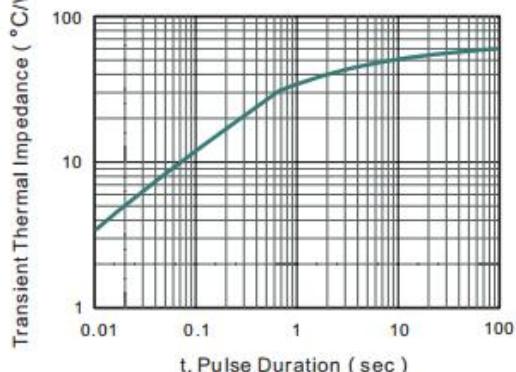
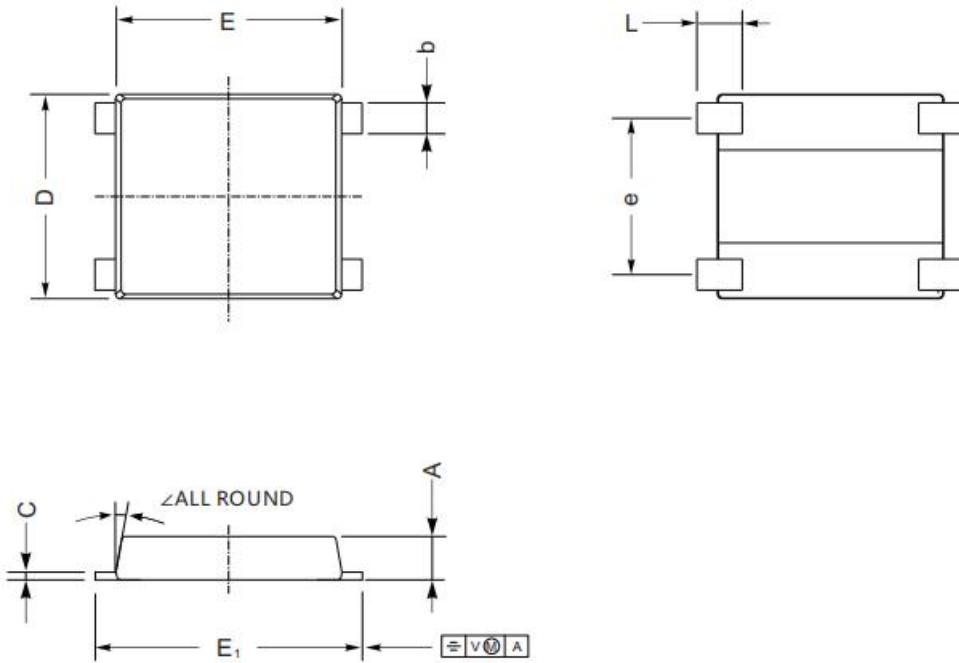


Fig.6- Typical Transient Thermal Impedance



■ Dimension 外形封装尺寸



UMSB mechanical data

UNIT		A	C	D	E	E ₁	L	e	b	∠
mm	max	1.5	0.29	7.0	7.6	8.9	1.6	5.3	1.15	10°
	min	1.3	0.17	6.2	7.1	8.4	1.0	4.9	0.95	
mil	max	59	12	276	299	350	55	209	45	10°
	min	51	7	244	280	331	31.5	193	37	